



The D30NA30Z4 is a high performance Aluminum Nitride (AIN) chip attenuator intended as a cost competitive alternative to Beryllium Oxide (BeO). The attenuator is well suited to all cellular frequency bands such as; AMPS, GSM, DCS, PCS, PHS and UMTS. The high power handling makes the part ideal for inter-stage matching, directional couplers, and for use in isolators. The attenuator is also RoHS compliant!

Features:

- RoHS Compliant
- 30 Watts
- Low Cost
- DC 3.0GHz
- AIN Ceramic
- Non-Nichrome Resistive Element
- Low VSWR
- 100% Tested

General Specifications

Resistive Element Thick film
Substrate AIN Ceramic

Terminal Finish Matte Tin over Nickel Barrier

Operating Temperature -55 to +200°C (see de rating chart)

Tolerance is ±0.010", unless otherwise specified. Designed to meet or exceed applicable portions of MIL-E-5400. **All dimensions in inches**.

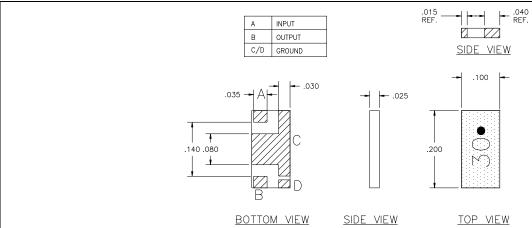
Electrical Specifications

Attenuation Value: 30dB +1dB, -1dB; DC - 2.7GHz +1dB, -1.5dB; DC - 3.0GHz

Power: 30 Watts
Frequency Range: DC – 3.0GHz
Input Return Loss: 20dB

Specification based on unit properly installed using suggested mounting instructions and a 50 ohm nominal impedance. **Specifications subject to change.**

Outline Drawing



PAD A CAN ONLY BE USED AS INPUT

PAD B CAN ONLY BE USED AS OUTPUT

UNLESS OTHERWISE SPECIFIED ALL DIMENSIONS ARE IN INCHES

THE BOTTOM GROUND PLANE (C&D) IS SHOWN "SPLIT". THIS IS <u>ONLY</u> FOR MANUFACTURING PURPOSES. PCB LAYOUT SHOULD BE DESIGNED TO HAVE ONE CONTINUOUS GROUND PLANE.

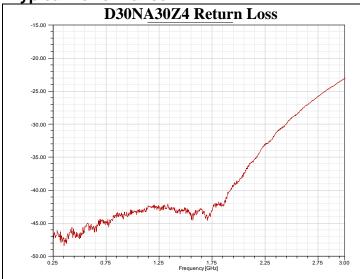


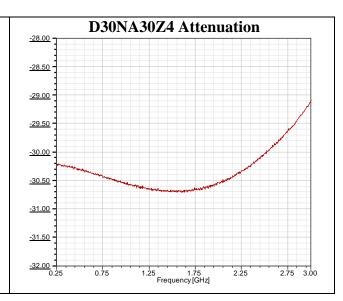
USA/Canada: Toll Free: Europe: (315) 432-8909 (800) 544-2414 +44 2392-232392

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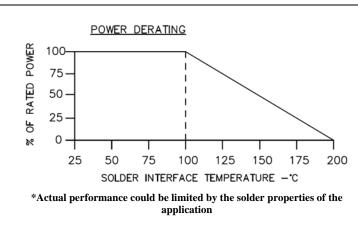


Typical Performance:

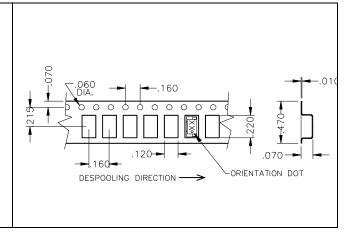




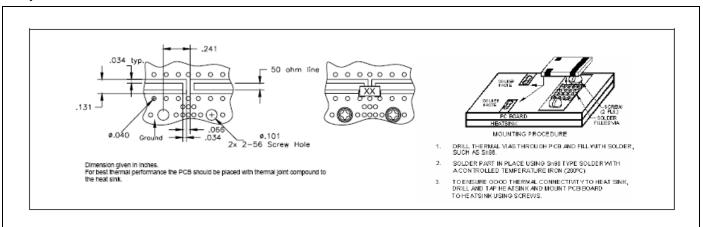
Power De-rating:



Mounting Footprint:



Tape and Reel:



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